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Intellectual Property Office Written Decision on Registration

A p p l i c a n t N a m e SAMSUNG ELECTRONICS CO., LTD. (patent client number:
119981042713)

A d d r e s s

A g e n t N a m e Y.P.LEE,MOCK&PARTNERS

A d d r e s s

D e s i g n a t e d a person besides Lee Young Pil

p a t e n t

a t t o r n e y

I n v e n t o r N a m e KIM, Yong Hun

A d d r e s s

I n v e n t o r N a m e DOO, Su Yeon

A d d r e s s

I n v e n t o r N a m e KANG, Dong Seok

A d d r e s s

I n v e n t o r N a m e KWON, Hye Jung

A d d r e s s

I n v e n t o r N a m e KIM, Young Ju

A d d r e s s

A p p l i c a t i o n N o 10-2017-0113355

T i t l e o f I n v e n t i o n Memory device having detection clock pattern generator
for generating detection clock output signal with random
data patterns

N u m b e r o f c l a i m s 19

This is to certify that the application was granted for a patent under Article 66 of Patent Act.

(By the patent right paying the patent fee and receiving the registration according to the article 87 of Patent Act it is generated) End.

[Priority Claim]

Priority Country: KR, and the priority claim No:1020170095718(priority date:

Netlist EX2025

Samsung v. Netlist

IPR2025-01402

2017.07.27)

Priority Country: KR, and the priority claim No:1020170089851(priority date: 2017.07.14)

[Reference]

1. KR100819097 B1
2. KR1020120095221 A
3. KR1020140039948 A
4. US20120023363 A1
5. KR1020170005250 A

[Official authority correction details]

Number	Correction member	Corrected position	Correction overall contents	The correction propriety	Drawing contents of amendment
			After correction content		
1	Claims	Claim 3	As for claim 1 The memory device in which the second rate soaks with $1/2 n$ (the n is the natural number more than 1) of the first rate.	The basic mistyping	X
			As for claim 1 The memory device in which the second rate soaks with $1/2 n$ (the n is the natural number more than 1) of the first rate.		
2	Claims	Claim 11	As for claim 10 The memory device in which the second rate soaks with $1/2 n$ (the n is the natural number more than 1) of the first rate.	The basic mistyping	X
			As for claim 10 The memory device in which the second rate soaks with $1/2 n$ (the n is the natural number more than 1) of the first rate.		